

## Supplementary Material

### Density Functional Study on ALD precursors for Hexagonal Boron Nitride Deposition

Naoya Uene<sup>a,b\*</sup>, Takuya Mabuchi<sup>b,c</sup>, Jin Yong<sup>d</sup>,

Masaru Zaitzu<sup>d</sup>, Shigeo Yasuhara<sup>d</sup>, Takashi Tokumasu<sup>b</sup>

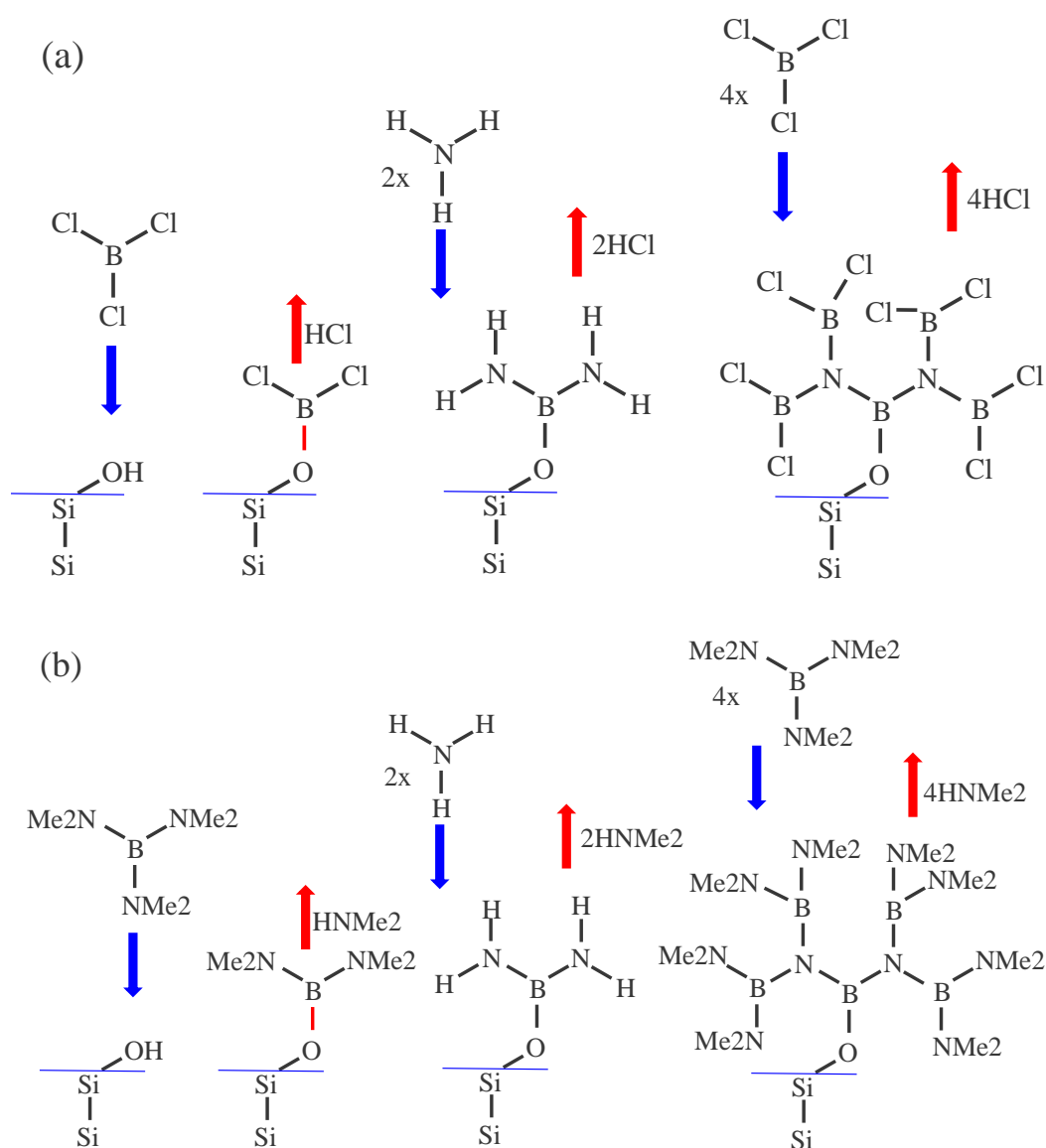
<sup>a</sup> Graduate School of Engineering Tohoku University, 2-1-1, Katahira, Aoba-ku, Sendai, Japan

<sup>b</sup> Institute of Fluid Science, Tohoku University, 2-1-1, Katahira, Aoba-ku, Sendai, Japan

<sup>c</sup> Frontier Research Institute of Interdisciplinary Sciences, Tohoku University, 2-1-1, Katahira, Aoba-ku, Sendai, Japan

<sup>d</sup> Japan Advanced Chemicals Ltd., 3007-4, Kamiechi, Atsugi, Kanazawa, Japan

\*Corresponding author. E-mail: uene@nanoint.ifs.tohoku.ac.jp (Naoya Uene)



**Figure S1.** Expected ALD growth mechanisms of BN by (a)  $\text{BCl}_3/\text{NH}_3$  and (b)  $\text{B}(\text{NMe}_2)_3/\text{NH}_3$ .